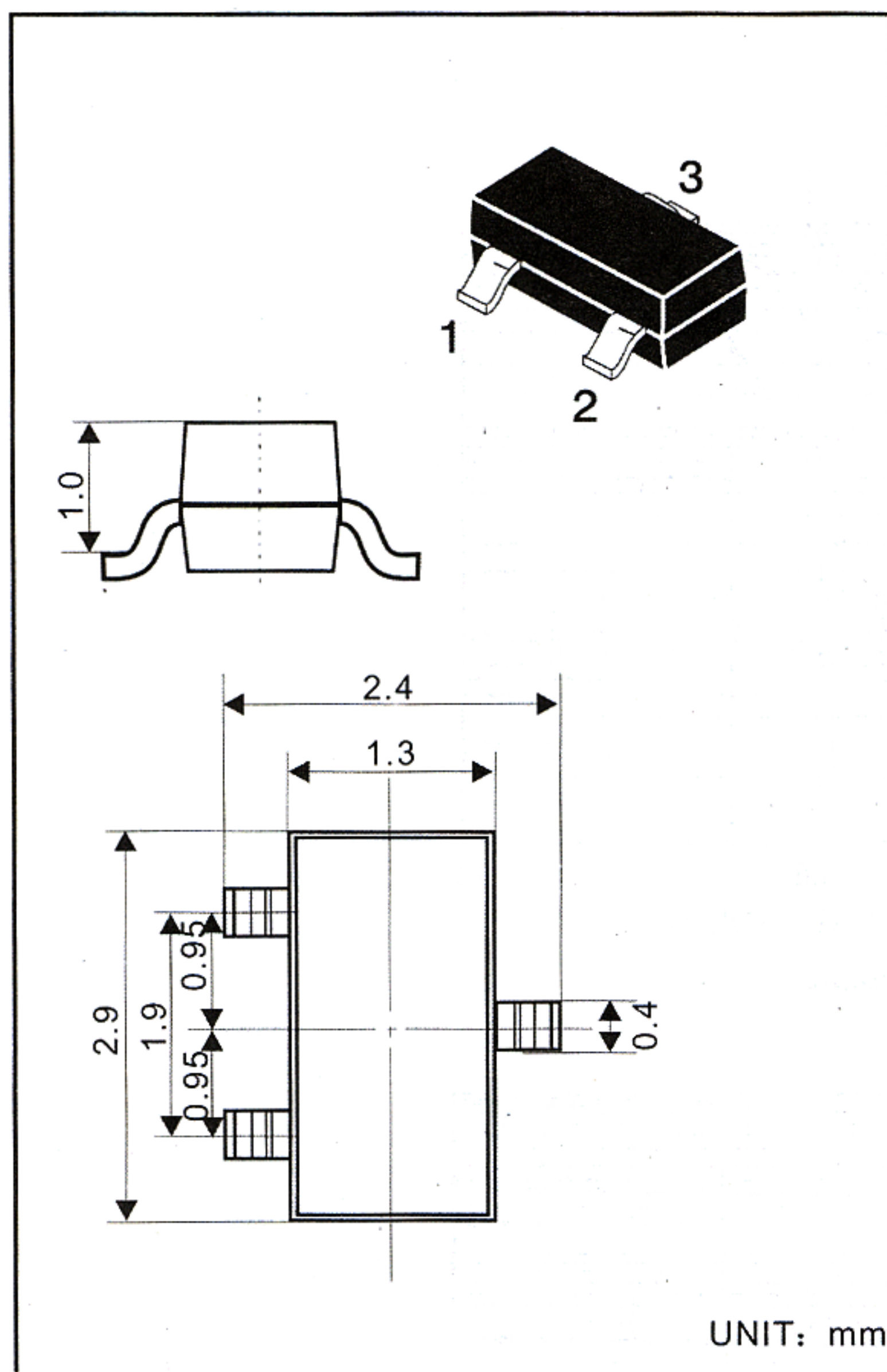


## BAV99LT1 SWITCHING DIODE



### FEATURES

#### Power dissipation

$P_D$ : 225mW ( $T_{amb}=25^\circ\text{C}$ )

#### Forward current

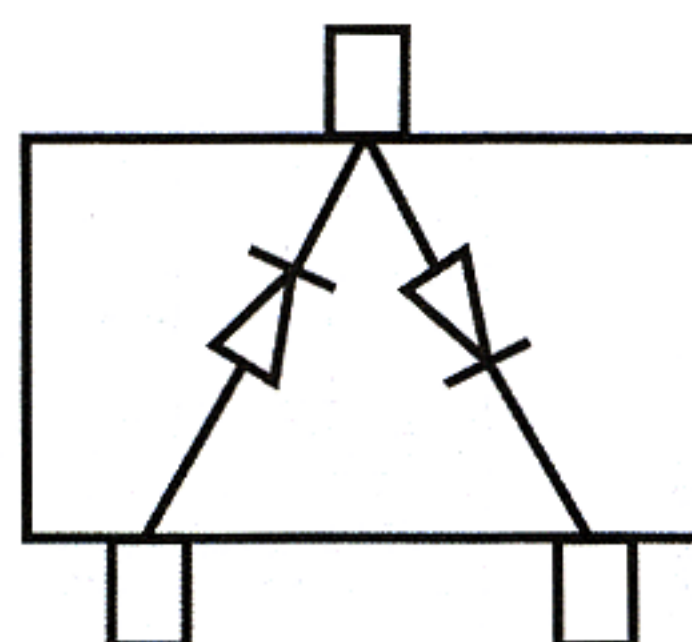
$I_F$ : 215mA

#### Reverse voltage

$V_R$ : 70V

#### Operating and storage junction temperature range

$T_J, T_{stg}$ :  $-55^\circ\text{C}$  to  $+150^\circ\text{C}$



MARKING: A7

### ELECTRICAL CHARACTERISTICS

( $T_{amp}=25^\circ\text{C}$  unless otherwise specified)

| Parameter                       | Symbol     | Test conditions                                                                  | MIN | MAX                        | UNIT          |
|---------------------------------|------------|----------------------------------------------------------------------------------|-----|----------------------------|---------------|
| Reverse breakdown voltage       | $V_{(BR)}$ | $I_R=100\mu\text{A}$                                                             | 70  |                            | V             |
| Reverse voltage leakage current | $I_R$      | $V_R=70\text{V}$                                                                 |     | 2.5                        | $\mu\text{A}$ |
| Forward voltage                 | $V_F$      | $I_F=1\text{mA}$<br>$I_F=10\text{mA}$<br>$I_F=50\text{mA}$<br>$I_F=150\text{mA}$ |     | 715<br>855<br>1000<br>1250 | mV            |
| Diode capacitance               | $C_{tot}$  | $V_R=0\text{V}, f=1\text{MHz}$                                                   |     | 1.5                        | pF            |
| Reverse recovery time           | $t_{rr}$   | $I_F=I_R=10\text{mA}$<br>$I_{rr}=0.1I_R$                                         |     | 6                          | ns            |

